

AN INTEGRATED DEVICE WITH A TRENCH ISOLATION STRUCTURE, AND
FABRICATION PROCESS THEREFOR

ABSTRACT OF THE DISCLOSURE

An integrated device having a substrate wherein a buried layer and an epitaxial region have been formed, and an isolation structure adapted to define a plurality of isolation wells for integrating the components of the integrated device therein, the isolation structure including plural dielectrically insulated regions or dielectric trenches being filled with a conductive material to form a plurality of contact regions to buried regions of the device, the buried regions including, in particular, the substrate and buried layer.

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